

## Electronic Supplementary Information

### **Bridging the gap: An in-depth comparison of the CVT-grown layered transition metal dichalcogenides for supercapacitor application**

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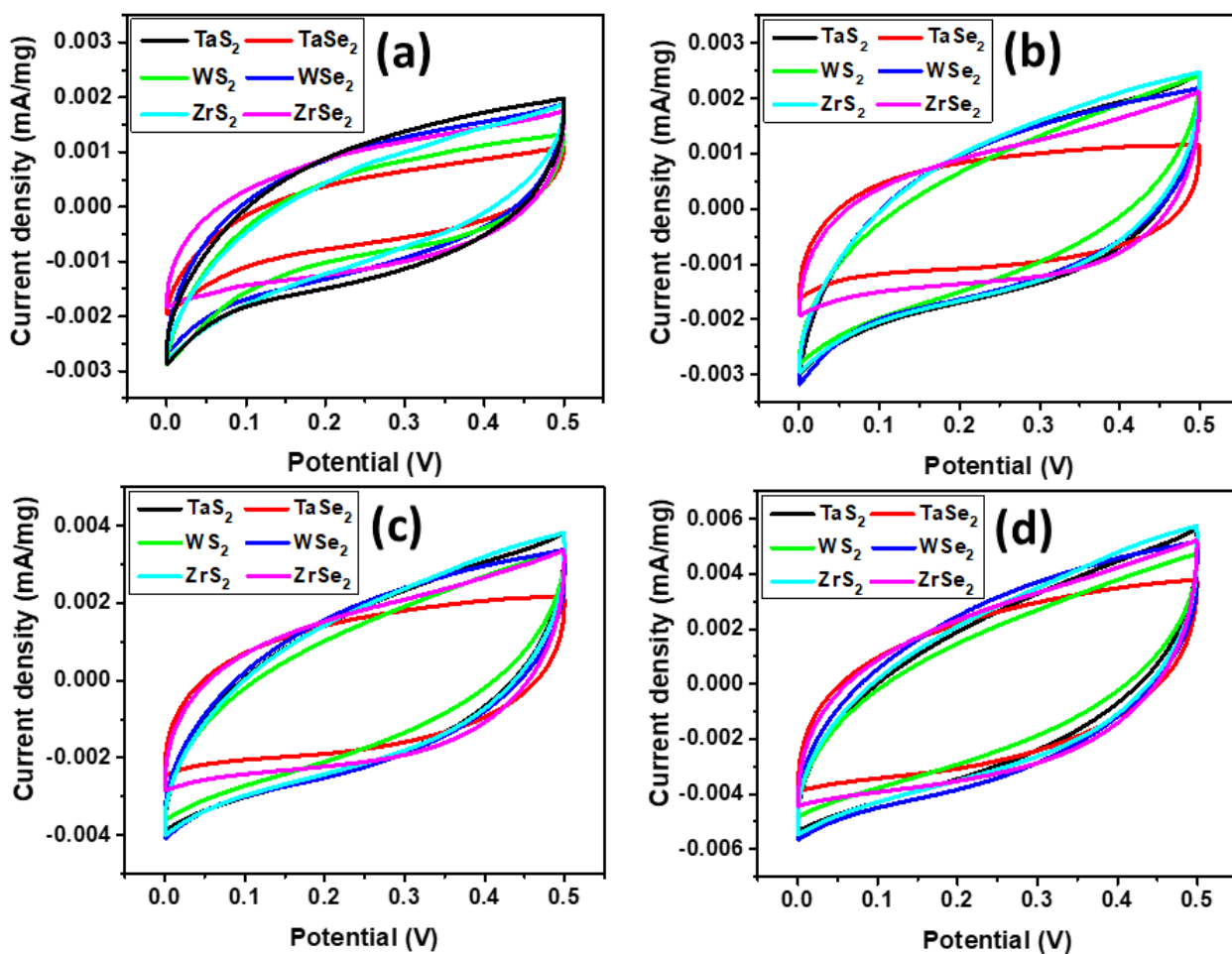
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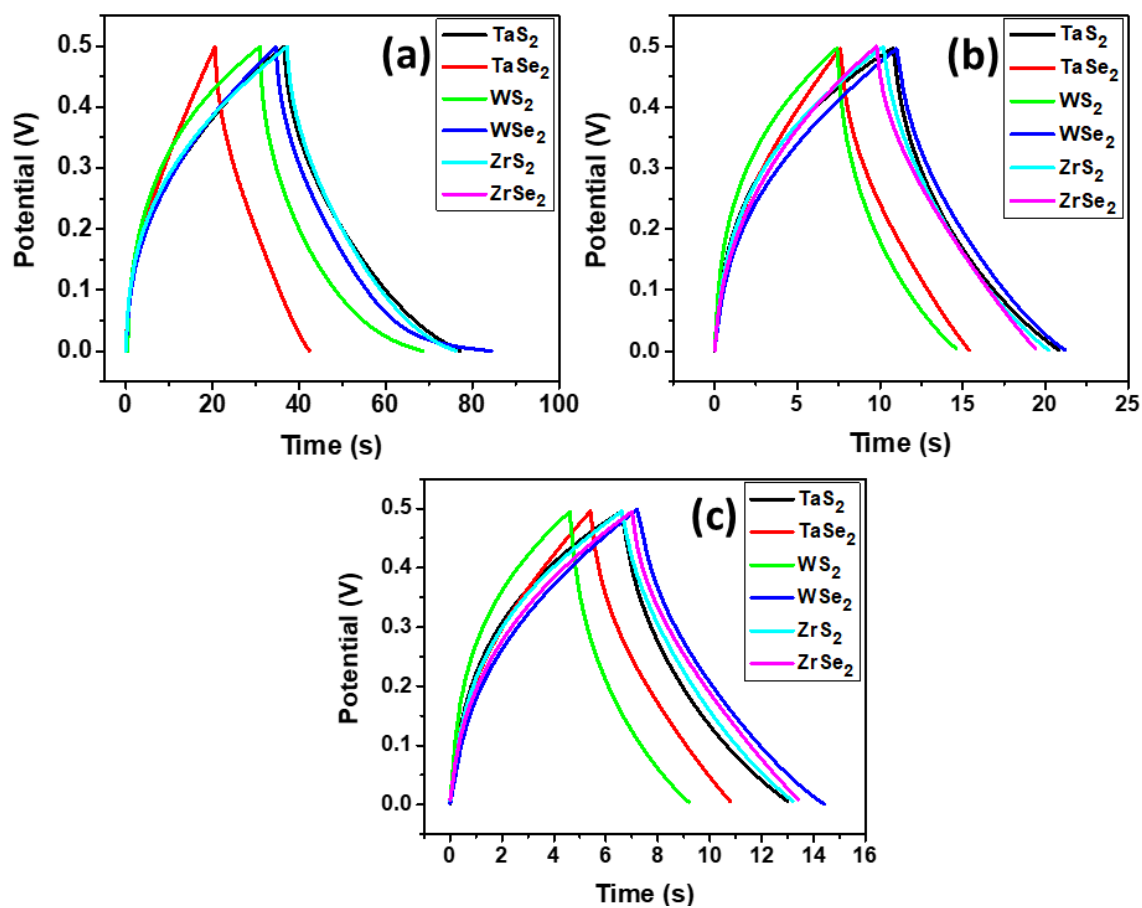
muhammad.habib@cuilahore.edu.pk (Muhammad Habib)

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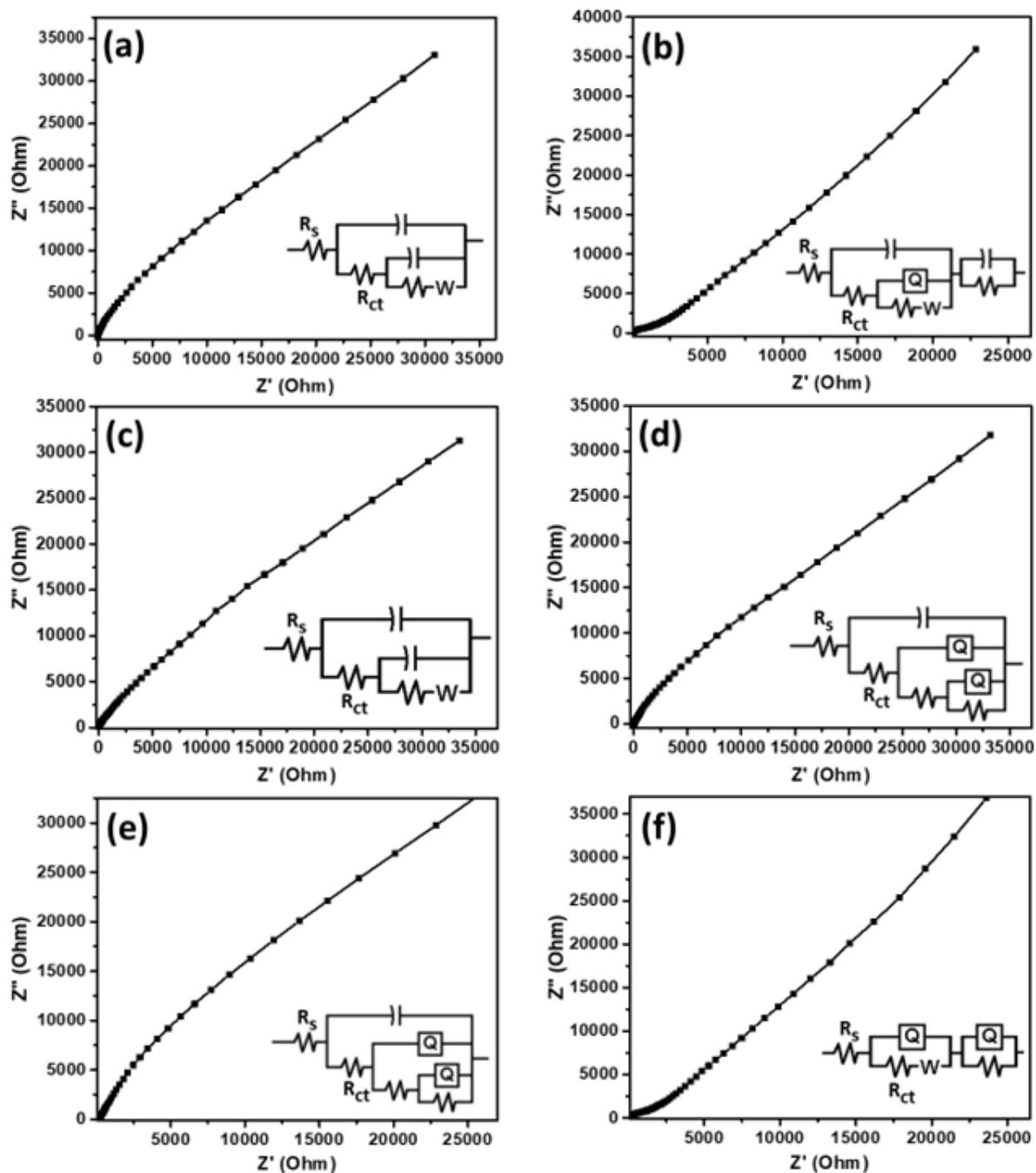
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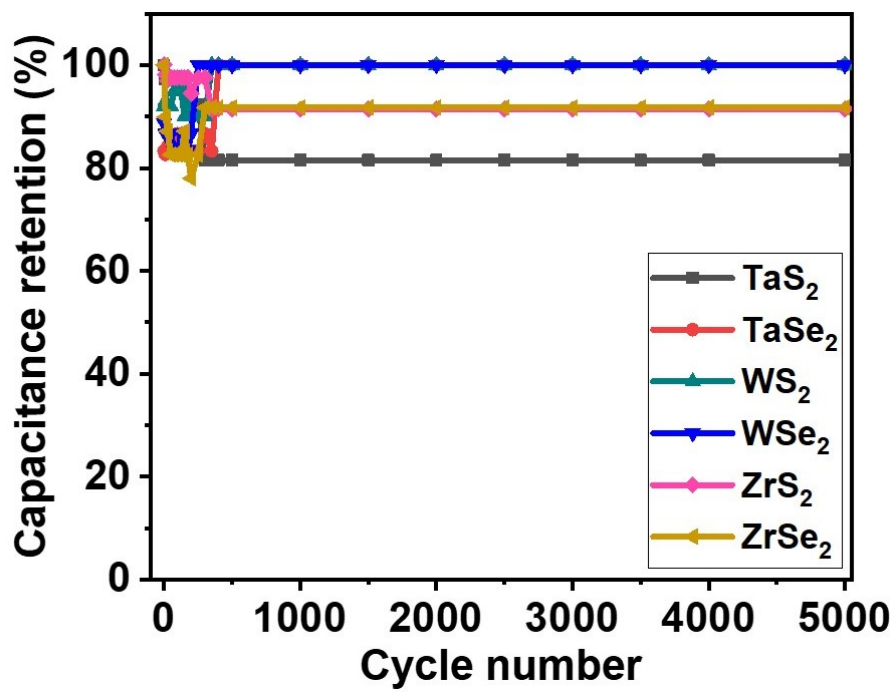
**Figure S1.** Cyclic voltammetry of the prepared electrodes at (a) 5, (b) 10, (c) 20 and (d) 40 mV/s scan rates.



**Figure S2.** Galvanostatic charge-discharge curves measured at (a) 0.2 A/g, (b) 0.4 A/g and (c) 0.5 A/g current densities.



**Figure S3.** Electrochemical impedance spectroscopy plots of (a)  $\text{TaS}_2$ , (b)  $\text{TaSe}_2$ , (c)  $\text{WS}_2$ , (d)  $\text{WSe}_2$ , (e)  $\text{ZrS}_2$  and (f)  $\text{ZrSe}_2$  with inset circuit models.



**Figure S4.** Combine stability curves of all the electrodes.

**Table S1:** A comparison of calculated gravimetric specific capacitances by both CV and GCD.

<b>S #</b>	<b>Material</b>	<b>Capacitance calculated by CV</b>	<b>Capacitance calculated by GCD</b>
<b>1</b>	TaS <sub>2</sub>	230 F/g	187 F/g
<b>2</b>	TaSe <sub>2</sub>	168 F/g	89 F/g
<b>3</b>	WS <sub>2</sub>	186 F/g	154 F/g
<b>4</b>	WSe <sub>2</sub>	224 F/g	203 F/g
<b>5</b>	ZrS <sub>2</sub>	225 F/g	183 F/g
<b>6</b>	ZrSe <sub>2</sub>	209 F/g	159 F/g